



#### **Product Summary**

BV <sub>DSS</sub>	RDS(ON) max	I <sub>D</sub> max T <sub>A</sub> = +25°C
2014	45mΩ @ V <sub>GS</sub> = 4.5V	4.5A
20V	55mΩ @ V <sub>GS</sub> = 2.5V	4.1A

## Description

This MOSFET has been designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## **Applications**

- Battery Charging
- Power Management Functions
- DC-DC Converters
- Portable Power Adaptors

#### **DUAL N-CHANNEL ENHANCEMENT MODE MOSFET**

## **Features and Benefits**

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative. <u>https://www.diodes.com/quality/product-definitions/</u>

## **Mechanical Data**

- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208@4

G2

Internal Schematic

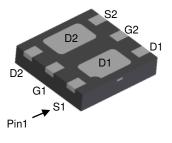
**D2** 

**S2** 

Weight: 0.0065 grams (Approximate)

D1

**S1** 



U-DFN2020-6 (Type B)

Bottom View

## Ordering Information (Note 4)

Part Number	Case	Packaging
DMN2050LFDB -7	U-DFN2020-6 (Type B)	3,000/Tape & Reel
DMN2050LFDB -13	U-DFN2020-6 (Type B)	10,000/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.</p>

G1

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



### **Marking Information**

Site 1



 $\begin{array}{l} M5 = Product Type Marking Code \\ YM = Date Code Marking \\ Y = Year (ex: H = 2020) \\ M = Month (ex: 9 = September) \end{array}$ 

Date Code Kev

Year	2013		2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	Α		Н	I	J	K	L	М	Ν	0	Р	R
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec

Site 2



M5 = Product Type Marking Code YWX = Date Code Marking

Y = Y ear (ex: 0 = 2020)W = Week (ex: a = week 27; z represents week 52 and 53)

X = Internal Code (ex: U = Monday)

Date Code Key												
Year	2013		2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	3		0	1	2	3	4	5	6	7	8	9
Week		1-26			27-52				53			
Code		ŀ	λ-Ζ			а	-Z			Z	2	
Internal Code	Sur	ı 🗌	Mon		Tue	W	ed	Thu		Fri		Sat
Code	T U			V	\	N	Х		Y		Z	



### Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	VDSS	20	V		
Gate-Source Voltage	V <sub>GSS</sub>	±12	V		
Continuous Drain Current (Note 5) $V_{GS}$ = 4.5V	Steady State	TA = +25°C TA = +70°C	lо	3.3 2.6	А
Continuous Drain Current (Note 6) $V_{GS} = 4.5V$ State $T_A = +25$ $T_A = +70$			lo	4.5 3.6	А
Maximum Continuous Body Diode Forward Curren	nt (Note 6)		ls	1	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1	ldм	25	А		
Avalanche Current (Note 7) L = 0.1mH	IAS	9	А		
Avalanche Energy (Note 7) L = 0.1mH			Eas	4.5	mJ

## **Thermal Characteristics**

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	$T_A = +25^{\circ}C$	D-	0.73	W
Total Fower Dissipation (Note 5)	$T_A = +70^{\circ}C$	PD	0.46	vv
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	Deve	173	°C/W
mermai Resistance, Sunction to Ambient (Note 5)	t<10s	RθJA	110	0/11
Total Power Dissipation (Note 6)	T <sub>A</sub> = +25°C	PD	1.42	W
Total Fower Dissipation (Note 0)	T <sub>A</sub> = +70°C	FD	0.90	vv
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	Dave	89	
memai resistance, sunction to Ambient (Note o)	t<10s	Reja	57	°C/W
Thermal Resistance, Junction to Case (Note 6)	Rejc	18		
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

## Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BVDSS	20	—		V	$V_{GS} = 0V, I_D = 250 \mu A$	
Zero Gate Voltage Drain Current TJ = +25°C	IDSS	_	—	1.0	μA	$V_{DS} = 16V, V_{GS} = 0V$	
Gate-Source Leakage	IGSS	_	—	±100	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	0.4	—	1.0	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance			28	45	mΩ	$V_{GS} = 4.5V, I_{D} = 5.0A$	
Static Drain-Source On-Resistance	RDS (ON)	_	36	55	11122	V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 4.2A	
Forward Transfer Admittance	Y <sub>fs</sub>		9	_	S	$V_{DS} = 5V, I_D = 5A$	
Diode Forward Voltage	Vsd		0.75	1.0	V	$V_{GS} = 0V$ , $I_{S} = 1A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	Ciss		389	_	pF		
Output Capacitance	Coss	_	72	_	pF	$V_{DS} = 10V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	Crss		63	_	pF		
Gate Resistance	Rg		2.1	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Qg	_	5.7	_	nC		
Total Gate Charge (V <sub>GS</sub> = 10V)	Qg	_	12		nC		
Gate-Source Charge	Q <sub>gs</sub>	_	0.7	_	nC	VDS = 15V, ID = 5.8A	
Gate-Drain Charge	Q <sub>gd</sub>	_	1.5	_	nC		
Turn-On Delay Time	td(on)	—	5	_	ns		
Turn-On Rise Time	t <sub>R</sub>	_	8	_	ns	$V_{DS} = 10V, V_{GS} = 4.5V,$	
Turn-Off Delay Time	tD(OFF)		25		ns	R <sub>G</sub> = 6Ω, I <sub>DS</sub> = 1A	
Turn-Off Fall Time	tF		8		ns	7	
Reverse Recovery Time	trr		8.5	—	ns		
Reverse Recovery Charge	QRR		2.1		nC	IF = 5A, di/dt = 100A/μs	

 Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate. Notes:

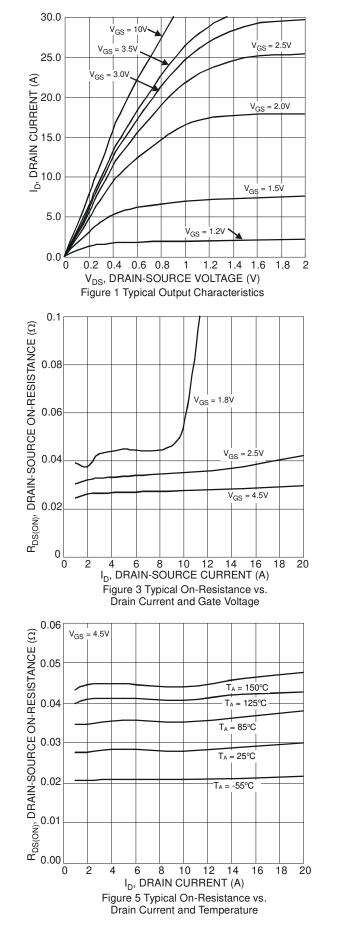
7.  $I_{AS}$  and  $E_{AS}$  ratings are based on low frequency and duty cycles to keep  $T_J = +25^{\circ}C$ .

8. Short duration pulse test used to minimize self-heating effect.

9. Guaranteed by design. Not subject to product testing.



## DMN2050LFDB



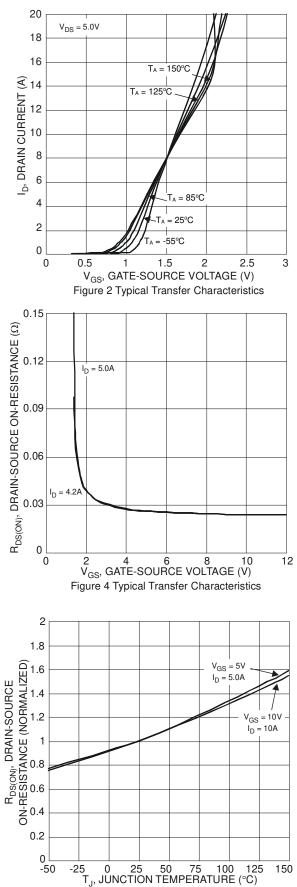
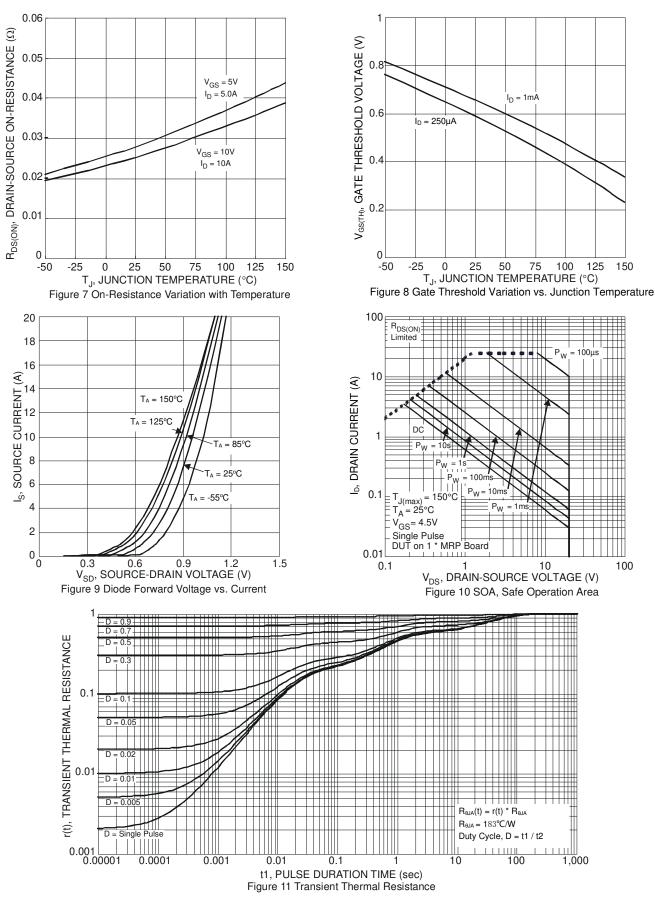


Figure 6 On-Resistance Variation with Temperature

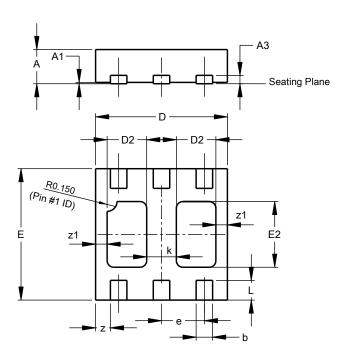






# Package Outline Dimensions

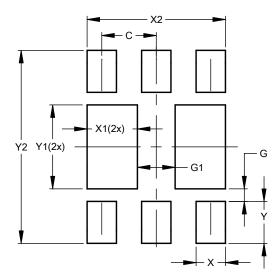
Please see http://www.diodes.com/package-outlines.html for the latest version.



	U-DFN	2020-6	
	Тур	e B	
Dim	Min	Max	Тур
Α	0.545	0.605	0.575
A1	0.00	0.05	0.02
A3	-	-	0.13
b	0.20	0.30	0.25
D	1.95	2.075	2.00
D2	0.50	0.70	0.60
е	-	-	0.65
Е	1.95	2.075	2.00
E2	0.90	1.10	1.00
k	-	-	0.45
L	0.25	0.35	0.30
z	-	-	0.225
z1	-	-	0.175
All	Dimens	ions in	mm

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.



#### U-DFN2020-6 (Type B)

U-DFN2020-6 (Type B)

Dimensions	Value (in mm)		
С	0.650		
G	0.150		
G1	0.450		
X	0.350		
X1	0.600		
X2	1.650		
Y	0.500		
Y1	1.000		
Y2	2.300		



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